

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L5	10	(trench adj isolation same active adj area near10 layer near5 densifying same silicon adj oxide adj liner same fill\$4 adj trench adj silicon adj oxide liner near5 deposit adj first adj buried adj layer near5 silicon oxide same second adj buried adj layer same silicon adj oxide layer adj upper adj layer same recess adj etch\$4)	US-PGPUB; USPAT	OR	OFF	2007/09/06 14:41
S1	13	(semiconductor adj trench adj isolation)	US-PGPUB; USPAT	OR	OFF	2006/06/26 09:38
S2	8773	(semiconductor near20 trench near20 isolat\$4)	US-PGPUB; USPAT	OR	OFF	2006/06/26 09:13
S3	5	S2 and (trench-etch\$4 near20 pattern\$4)	US-PGPUB; USPAT	OR	OFF	2006/06/26 09:14
S4	6	S2 and (trench-etch)	US-PGPUB; USPAT	OR	OFF	2006/06/26 09:15
S5	29	S2 and (trench\$1etch\$4)	US-PGPUB; USPAT	OR	OFF	2006/06/26 09:31
S6	19	S5 and (etch\$4 near5 mask)	US-PGPUB; USPAT	OR	OFF	2006/06/26 09:27
S7	17	S6 and (SiN or (silicon adj nitride))	US-PGPUB; USPAT	OR	OFF	2006/06/26 09:17
S8	13	S7 and (silicon adj oxide)	US-PGPUB; USPAT	OR	OFF	2006/06/26 09:17
S9	7	S8 and (heat near20 treat\$4)	US-PGPUB; USPAT	OR	OFF	2006/06/26 09:18
S10	4	S9 and (HTO near5 layer\$4)	US-PGPUB; USPAT	OR	OFF	2006/06/26 09:20
S11	4	S10 and (wet near5 etch\$4)	US-PGPUB; USPAT	OR	OFF	2006/06/26 09:20
S12	0	S2 and (spin adj on adj glass)	US-PGPUB; USPAT	OR	OFF	2006/06/26 09:32
S13	2	(("4798629") or ("6743712")).PN.	US-PGPUB; USPAT	OR	OFF	2006/06/26 09:38
S14	10	(("4631803") or ("5435888") or ("5801083") or ("6187651") or ("6194283") or ("6228742") or ("6258697") or ("6333218") or ("6339004") or ("6391738")).PN.	US-PGPUB; USPAT	OR	OFF	2006/06/26 10:57
S15	0	S14 and S11	US-PGPUB; USPAT	OR	OFF	2006/06/26 10:58

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S16	0	S14 and S9	US-PGPUB; USPAT	OR	OFF	2006/06/26 10:58
S17	0	S14 and S1	US-PGPUB; USPAT	OR	OFF	2006/06/26 10:58
S18	10	("4631803"   "5435888"   "5801083"   "6187651"   "6194283"   "6228742"   "6258697"   "6333218"   "6339004"   "6391738").PN. OR ("6683354"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/06/26 12:30
S19	4	(("6566229") or ("6593207") or ("6756654") or ("6740955")).PN.	US-PGPUB; USPAT	OR	OFF	2006/06/26 12:31
S20	18	("20020055271"   "20020063334"   "20020072198"   "20020072246"   "20020127817"   "20020168873"   "6194283"   "6232216"   "6294833"   "6489252").PN. OR ("6566229"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/06/26 12:34
S21	5	("20020072198"   "20020076879"   "5937292"   "6127241").PN. OR ("6740955").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/06/26 12:44
S22	1	("5728621").PN.	US-PGPUB; USPAT	OR	OFF	2006/06/26 15:34
S23	1	("5770260").PN.	US-PGPUB; USPAT	OR	OFF	2006/06/26 15:34
S24	4896	438/690,424,435,701,720. 978;257/397,510,522;216/80,97. ccls.	US-PGPUB; USPAT	OR	OFF	2006/06/27 09:42
S25	8795	(semiconductor near20 trench near20 isolat\$4)	US-PGPUB; USPAT	OR	OFF	2006/06/27 09:42
S26	29	S25 and (trench\$1etch\$4)	US-PGPUB; USPAT	OR	OFF	2006/06/27 09:42
S27	19	S26 and (etch\$4 near5 mask)	US-PGPUB; USPAT	OR	OFF	2006/06/27 09:42
S28	10	S24 and S27	US-PGPUB; USPAT	OR	OFF	2006/06/27 09:42
S29	1	("6051480").PN.	US-PGPUB; USPAT	OR	OFF	2006/10/27 12:35